

Schottky barrier diode

RB886G

●Applications

High frequency detection

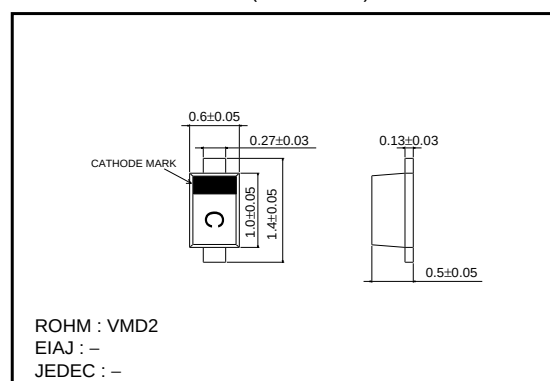
●Features

- 1) Small mold type. (VMD2)
- 2) Low C_t and high detection efficiency.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage	V_R	5.0	V
Forward current	I_F	10	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.35	V	$I_F=1.0\text{mA}$
Reverse current	I_R	—	—	120	μA	$V_R=5.0\text{V}$
Capacitance between terminal	C_T	—	0.53	0.80	pF	$V_R=1.0\text{V}$, $f=1.0\text{MHz}$

* Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

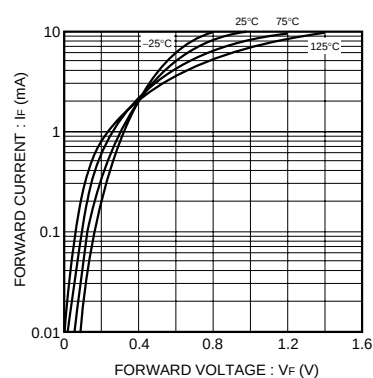


Fig.1 Forward characteristics

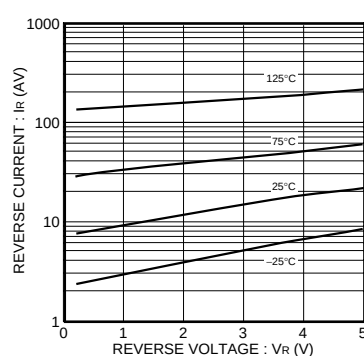


Fig.2 Reverse characteristics

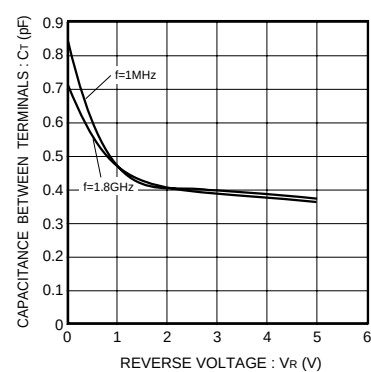


Fig.3 Capacitance between terminals characteristics

●Spice parameter

	Parameter	Value	Unit
1	IS : Saturation current	8.79631E-06	A
2	N : Emission coefficient	2.24097	—
3	RS : Ohmic resistance	6.20008	Ω
4	TT : Transit time	—	SEC
5	CJO : Junction capacitance	4.21E-13	F
6	M : Grading coefficient	0.346685	—
7	VJ : Junction potential	0.7	V
8	FC : Depretion cap. Coefficient	0.5	—
9	EG : Activation energy	1.11	eV
10	XTI : Isat temperature exponent	3	—
11	KF : Flicker noise coefficient	—	—
12	AF : Flicker noise exponent	—	—
13	BV : Reverse breakdown voltage	20	V
14	IBV : I at V-breakdown	—	A
15	RL : Junction leakage resistance	2.39557E+05	Ω